

TPS2290x 3.6-V, 500-mA, 78-mΩ ON-Resistance Load Switch With Controlled Turnon

1 Features

- Integrated P-Channel Load Switch
- Low Input Voltage: 1 V to 3.6 V
- ON-Resistance (Typical Values)
 - $r_{ON} = 78 \text{ m}\Omega$ at $V_{IN} = 3.6 \text{ V}$
 - $r_{ON} = 93 \text{ m}\Omega$ at $V_{IN} = 2.5 \text{ V}$
 - $r_{ON} = 109 \text{ m}\Omega$ at $V_{IN} = 1.8 \text{ V}$
 - $r_{ON} = 146 \text{ m}\Omega$ at $V_{IN} = 1.2 \text{ V}$
- 500 mA Maximum Continuous Switch Current
- Quiescent Current: 82 nA at 1.8 V
- Shutdown Current: 44 nA at 1.8 V
- Low Control Input Thresholds Enable Use of 1.2-V, 1.8-V, 2.5-V, and 3.3-V Logic
- Controlled Slew Rate to Avoid Inrush Currents
 - $t_r = 40 \mu\text{s}$ at $V_{IN} = 1.8 \text{ V}$ (TPS22901/2)
 - $t_r = 220 \mu\text{s}$ at $V_{IN} = 1.8 \text{ V}$ (TPS22902B)
- Quick Output Discharge (TPS22902/2B)
- ESD Performance Tested Per JESD 22
 - 2000-V Human Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
- Four-Pin Wafer-Chip-Scale DSBGA Package
 - 0.8-mm × 0.8-mm, 0.4-mm Pitch, 0.5-mm Height (YFP)

2 Applications

- Personal Digital Assistants (PDAs)
- Cellular Phones
- GPS Devices
- MP3 Players
- Digital Cameras
- Peripheral Ports
- Portable Instrumentation
- RF Modules

3 Description

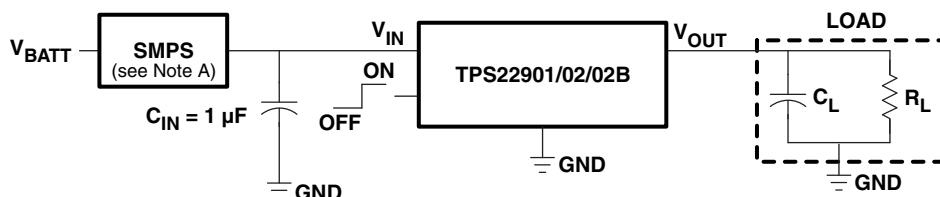
The TPS22901, TPS22902, and TPS22902B are small, low ON-resistance (r_{ON}) load switches with a controlled turnon. These devices contain a P-channel MOSFET that operates over an input voltage range of 1.0 V to 3.6 V. The switch is controlled by an on/off input (ON), which can interface directly with low-voltage control signals. In the TPS22902 and TPS22902B, an 88- Ω on-chip load resistor is added for output quick discharge when the switch is turned off.

The TPS22901, TPS22902, and TPS22902B are available in a space-saving 4-pin DSBGA (YFP) with 0.4-mm pitch. These devices are characterized for operation over the free-air temperature range of –40°C to 85°C.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
TPS22901		
TPS22902	DSBGA (4)	0.80 mm × 0.80 mm
TPS22902B		

(1) For all available packages, see the orderable addendum at the end of the data sheet.



A. Switched-mode power supply

Typical Application Schematic



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision D (January 2015) to Revision E (September 2020)	Page
• Updated the numbering format for tables, figures and cross-references throughout the document.....	1

Changes from Revision C (December 2012) to Revision D (January 2015)	Page
• Added <i>ESD Rating</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i> , <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section.....	1
• Deleted the <i>ORDERING INFORMATION</i> table.....	3

Changes from Revision B (March 2009) to Revision C (December 2012)	Page
• Changed the <i>ORDERING INFORMATION</i> table.....	3

5 Device Comparison Table

	R _{ON} at 1.8 V (TYP)	RISE TIME (TYP at 1.8 V)	QUICK OUTPUT DISCHARGE ⁽¹⁾	MAX OUTPUT CURRENT	ENABLE
TPS22901	109 mΩ	40 µs	No	500 mA	Active high
TPS22902			Yes		
TPS22902B		220 µs	Yes		

(1) This feature discharges the output of the switch to ground through an 88 Ω resistor, preventing the output from floating.

6 Pin Configuration and Functions

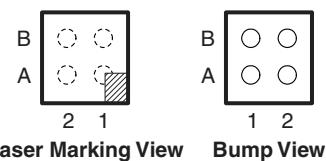


Figure 6-1. YFP Package 4-Pin DSBGA

Pin Assignments

B	ON	GND
A	V _{IN}	V _{OUT}
	2	1

Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
A1	V _{OUT}	O	Switch output
A2	V _{IN}	I	Switch input, bypass this input with a ceramic capacitor to ground
B1	GND	-	Ground
B2	ON	I	Switch control input, active high

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{IN}	Input voltage	-0.3	4	V
V _{OUT}	Output voltage		V _{IN} + 0.3	V
V _{ON}	Input voltage	-0.3	4	V
P	Power dissipation at T _A = 25°C		0.48	W
I _{MAX}	Maximum continuous switch current		500	mA
T _A	Operating free-air temperature	-40	85	°C
T _{lead}	Maximum lead temperature (10-s soldering time)		300	°C
T _{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under [Section 7.3](#). Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

		MIN	MAX	UNIT
V _{IN}	Input voltage	1	3.6	V
V _{OUT}	Output voltage		V _{IN}	V
V _{IH}	High-level input voltage, ON	0.85	3.6	V
V _{IL}	Low-level input voltage, ON		0.4	V
C _{IN}	Input capacitor	See ⁽¹⁾		μF

- (1) See [Section 10.1.1](#).

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS2290X	UNIT
		YFP (DSBGA)	
		4 PINS	
R _{θJA}		Junction-to-ambient thermal resistance	192.1
R _{θJC(top)}		Junction-to-case (top) thermal resistance	2.3
R _{θJB}		Junction-to-board thermal resistance	35.8
Ψ _{JT}		Junction-to-top characterization parameter	11.8
Ψ _{JB}		Junction-to-board characterization parameter	35.6

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

7.5 Electrical Characteristics

$V_{IN} = 1.0 \text{ V}$ to 3.6 V , $T_A = -40^\circ\text{C}$ to 85°C (unless otherwise noted). Typical values are for $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
I_Q	Quiescent current	$I_{OUT} = 0, V_{IN} = V_{ON}$	$V_{IN} = 1.1 \text{ V}$	Full	37	120	nA
			$V_{IN} = 1.8 \text{ V}$	Full	82	235	
			$V_{IN} = 3.6 \text{ V}$	Full	204	880	
$I_{IN(OFF)}$	OFF-state supply current	$V_{ON} = \text{GND}, V_{OUT} = \text{Open}$	$V_{IN} = 1.1 \text{ V}$	Full	22	210	nA
			$V_{IN} = 1.8 \text{ V}$	Full	44	260	
			$V_{IN} = 3.6 \text{ V}$	Full	137	700	
$I_{IN(LEAKAGE)}$	OFF-state switch current	$V_{ON} = \text{GND}, V_{OUT} = 0 \text{ V}$	$V_{IN} = 1.1 \text{ V}$	Full	22	140	nA
			$V_{IN} = 1.8 \text{ V}$	Full	45	230	
			$V_{IN} = 3.6 \text{ V}$	Full	137	610	
r_{ON}	ON-state resistance	$I_{OUT} = -200 \text{ mA}$	$V_{IN} = 3.6 \text{ V}$	25°C	78	95	mΩ
				Full		95	
			$V_{IN} = 2.5 \text{ V}$	25°C	93	110	
				Full		110	
			$V_{IN} = 1.8 \text{ V}$	25°C	109	130	
				Full		130	
			$V_{IN} = 1.2 \text{ V}$	25°C	146	200	
				Full		200	
			$V_{IN} = 1.1 \text{ V}$	25°C	174	330	
				Full		330	
r_{PD}	Output pulldown resistance	$V_{IN} = 3.3 \text{ V}, V_{ON} = 0, I_{OUT} = 30 \text{ mA}$ (TPS22902/TPS22902B only)	25°C		88	120	Ω
I_{ON}	ON input leakage current	$V_{ON} = 1.1 \text{ V}$ to 3.6 V or GND	Full		25	nA	

7.6 Switching Characteristics ($V_{IN} = 1.1\text{ V}$)

$V_{IN} = 1.1\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TPS22901			TPS22902 ⁽¹⁾			TPS22902B ⁽¹⁾			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{ON}	Turn-ON time $R_L = 500\ \Omega$	$C_L = 0.1\ \mu\text{F}$	108		108			531			μs
		$C_L = 1\ \mu\text{F}$	131		131			596			
		$C_L = 3.3\ \mu\text{F}$	153		153			659			
t_{OFF}	Turn-OFF time $R_L = 500\ \Omega$	$C_L = 0.1\ \mu\text{F}$	39		11			11			μs
		$C_L = 1\ \mu\text{F}$	317		69			67			
		$C_L = 3.3\ \mu\text{F}$	1105		238			225			
t_r	V_{OUT} rise time $R_L = 500\ \Omega$	$C_L = 0.1\ \mu\text{F}$	70		70			365			μs
		$C_L = 1\ \mu\text{F}$	78		78			367			
		$C_L = 3.3\ \mu\text{F}$	92		92			395			
t_f	V_{OUT} fall time $R_L = 500\ \Omega$	$C_L = 0.1\ \mu\text{F}$	107		18			21			μs
		$C_L = 1\ \mu\text{F}$	966		175			189			
		$C_L = 3.3\ \mu\text{F}$	3532		632			565			

(1) Quick Output Discharge

7.7 Switching Characteristics ($V_{IN} = 1.2\text{ V}$)

$V_{IN} = 1.2\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TPS22901			TPS22902 ⁽¹⁾			TPS22902B ⁽¹⁾			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{ON}	Turn-ON time $R_L = 500\ \Omega$	$C_L = 0.1\ \mu\text{F}$	96		96			471			μs
		$C_L = 1\ \mu\text{F}$	116		116			527			
		$C_L = 3.3\ \mu\text{F}$	135		135			587			
t_{OFF}	Turn-OFF time $R_L = 500\ \Omega$	$C_L = 0.1\ \mu\text{F}$	39		10			10			μs
		$C_L = 1\ \mu\text{F}$	317		62			61			
		$C_L = 3.3\ \mu\text{F}$	1110		210			199			
t_r	V_{OUT} rise time $R_L = 500\ \Omega$	$C_L = 0.1\ \mu\text{F}$	62		62			324			μs
		$C_L = 1\ \mu\text{F}$	69		69			325			
		$C_L = 3.3\ \mu\text{F}$	81		81			350			
t_f	V_{OUT} fall time $R_L = 500\ \Omega$	$C_L = 0.1\ \mu\text{F}$	109		17			20			μs
		$C_L = 1\ \mu\text{F}$	995		163			175			
		$C_L = 3.3\ \mu\text{F}$	3650		587			523			

(1) Quick Output Discharge

7.8 Switching Characteristics ($V_{IN} = 1.8$ V)

$V_{IN} = 1.8$ V, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TPS22901			TPS22902 ⁽¹⁾			TPS22902B ⁽¹⁾			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{ON}	Turn-ON time $R_L = 500 \Omega$	$C_L = 0.1 \mu\text{F}$	61		61			302			μs
		$C_L = 1 \mu\text{F}$	72		72			335			
		$C_L = 3.3 \mu\text{F}$	83		83			367			
t_{OFF}	Turn-OFF time $R_L = 500 \Omega$	$C_L = 0.1 \mu\text{F}$	38		8			8			μs
		$C_L = 1 \mu\text{F}$	317		49			49			
		$C_L = 3.3 \mu\text{F}$	1135		169			167			
t_r	V_{OUT} rise time $R_L = 500 \Omega$	$C_L = 0.1 \mu\text{F}$	40		40			220			μs
		$C_L = 1 \mu\text{F}$	45		45			220			
		$C_L = 3.3 \mu\text{F}$	53		53			235			
t_f	V_{OUT} fall time $R_L = 500 \Omega$	$C_L = 0.1 \mu\text{F}$	111		15			15			μs
		$C_L = 1 \mu\text{F}$	1020		140			159			
		$C_L = 3.3 \mu\text{F}$	3700		517			481			

(1) Quick Output Discharge

7.9 Switching Characteristics ($V_{IN} = 2.5$ V)

$V_{IN} = 2.5$ V, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TPS22901			TPS22902 ⁽¹⁾			TPS22902B ⁽¹⁾			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{ON}	Turn-ON time $R_L = 500 \Omega$	$C_L = 0.1 \mu\text{F}$	45		45			223			μs
		$C_L = 1 \mu\text{F}$	53		53			246			
		$C_L = 3.3 \mu\text{F}$	61		61			268			
t_{OFF}	Turn-OFF time $R_L = 500 \Omega$	$C_L = 0.1 \mu\text{F}$	38		7			7			μs
		$C_L = 1 \mu\text{F}$	314		46			47			
		$C_L = 3.3 \mu\text{F}$	1140		161			158			
t_r	V_{OUT} rise time $R_L = 500 \Omega$	$C_L = 0.1 \mu\text{F}$	32		32			175			μs
		$C_L = 1 \mu\text{F}$	35		35			175			
		$C_L = 3.3 \mu\text{F}$	41		41			187			
t_f	V_{OUT} fall time $R_L = 500 \Omega$	$C_L = 0.1 \mu\text{F}$	113		14			18			μs
		$C_L = 1 \mu\text{F}$	1040		139			185			
		$C_L = 3.3 \mu\text{F}$	3795		516			471			

(1) Quick Output Discharge

7.10 Switching Characteristics ($V_{IN} = 3.0\text{ V}$)

$V_{IN} = 3.0\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TPS22901			TPS22902 ⁽¹⁾			TPS22902B ⁽¹⁾			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{ON}	Turn-ON time $R_L = 500\text{ }\Omega$	$C_L = 0.1\text{ }\mu\text{F}$	38		38			191			μs
		$C_L = 1\text{ }\mu\text{F}$	45		45			211			
		$C_L = 3.3\text{ }\mu\text{F}$	53		53			231			
t_{OFF}	Turn-OFF time $R_L = 500\text{ }\Omega$	$C_L = 0.1\text{ }\mu\text{F}$	38		7			7			μs
		$C_L = 1\text{ }\mu\text{F}$	320		46			46			
		$C_L = 3.3\text{ }\mu\text{F}$	1145		53			156			
t_r	V_{OUT} rise time $R_L = 500\text{ }\Omega$	$C_L = 0.1\text{ }\mu\text{F}$	28		28			159			μs
		$C_L = 1\text{ }\mu\text{F}$	31		31			160			
		$C_L = 3.3\text{ }\mu\text{F}$	37		37			170			
t_f	V_{OUT} fall time $R_L = 500\text{ }\Omega$	$C_L = 0.1\text{ }\mu\text{F}$	114		14			17			μs
		$C_L = 1\text{ }\mu\text{F}$	1045		139			160			
		$C_L = 3.3\text{ }\mu\text{F}$	3815		509			473			

(1) Quick Output Discharge

7.11 Switching Characteristics ($V_{IN} = 3.6\text{ V}$)

$V_{IN} = 3.6\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TPS22901			TPS22902 ⁽¹⁾			TPS22902B ⁽¹⁾			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{ON}	Turn-ON time $R_L = 500\text{ }\Omega$	$C_L = 0.1\text{ }\mu\text{F}$	33		33			166			μs
		$C_L = 1\text{ }\mu\text{F}$	39		39			183			
		$C_L = 3.3\text{ }\mu\text{F}$	46		46			201			
t_{OFF}	Turn-OFF time $R_L = 500\text{ }\Omega$	$C_L = 0.1\text{ }\mu\text{F}$	38		7			7			μs
		$C_L = 1\text{ }\mu\text{F}$	322		46			45			
		$C_L = 3.3\text{ }\mu\text{F}$	1145		156			155			
t_r	V_{OUT} rise time $R_L = 500\text{ }\Omega$	$C_L = 0.1\text{ }\mu\text{F}$	25		25			146			μs
		$C_L = 1\text{ }\mu\text{F}$	28		28			146			
		$C_L = 3.3\text{ }\mu\text{F}$	34		34			156			
t_f	V_{OUT} fall time $R_L = 500\text{ }\Omega$	$C_L = 0.1\text{ }\mu\text{F}$	116		14			17			μs
		$C_L = 1\text{ }\mu\text{F}$	1060		139			161			
		$C_L = 3.3\text{ }\mu\text{F}$	3840		512			475			

(1) Quick Output Discharge

7.12 Typical Characteristics

7.12.1 Typical DC Characteristics

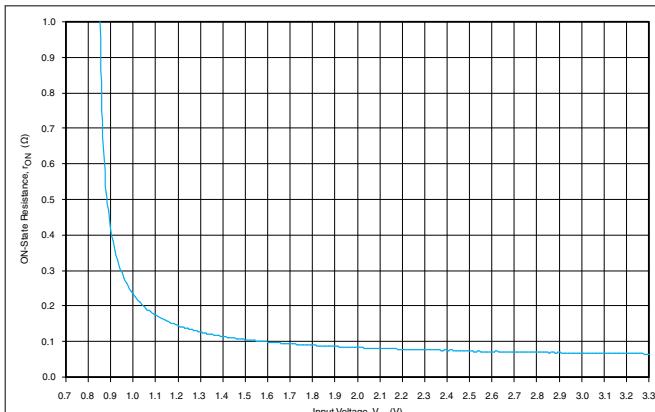


Figure 7-1. r_{ON} vs V_{IN}

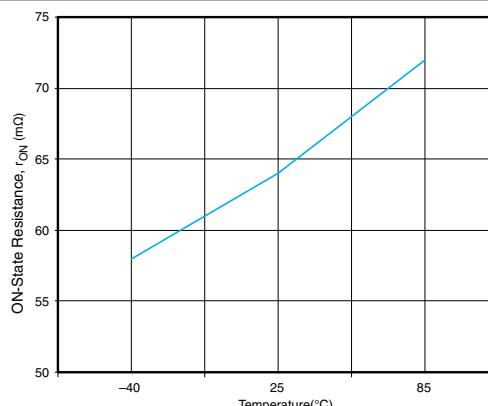


Figure 7-2. r_{ON} vs Temperature ($V_{IN} = 3.3$ V)

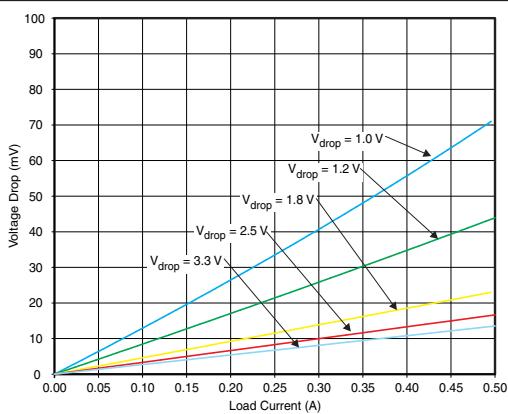


Figure 7-3. Voltage Drop vs. Load Current

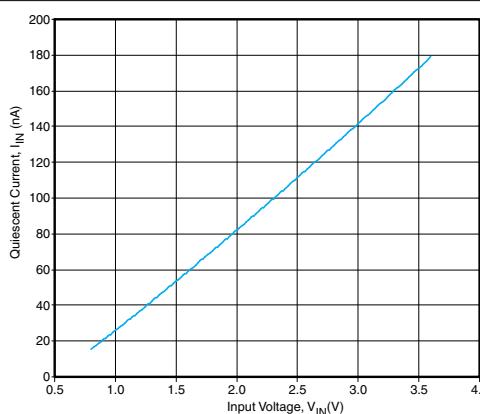


Figure 7-4. Quiescent Current vs V_{IN} ($V_{ON} = V_{IN}$, $I_{OUT} = 0$)

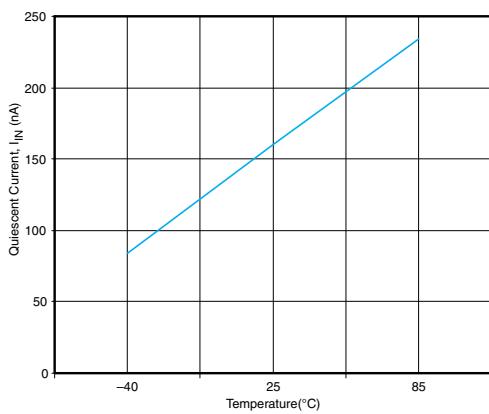


Figure 7-5. Quiescent Current vs Temperature ($V_{IN} = 3.3$ V, $I_{OUT} = 0$)

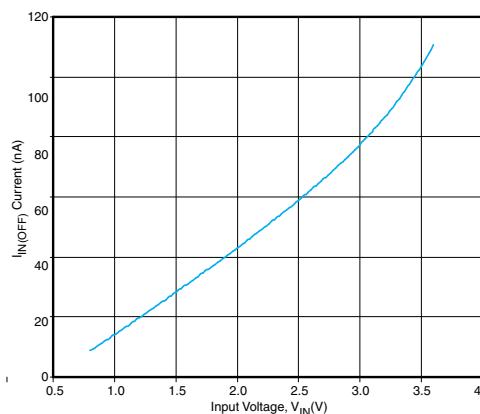
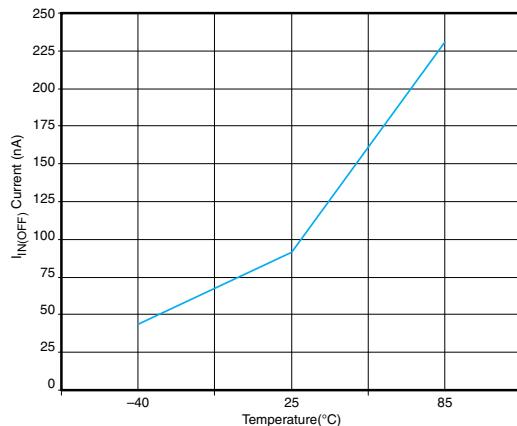
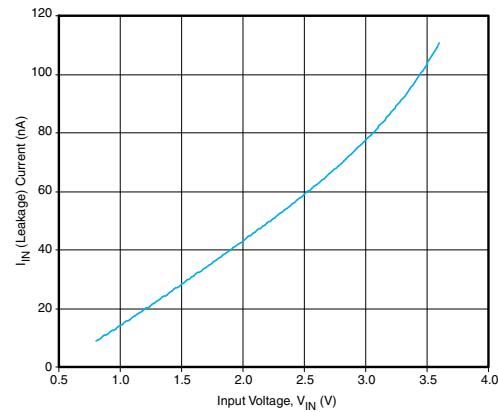
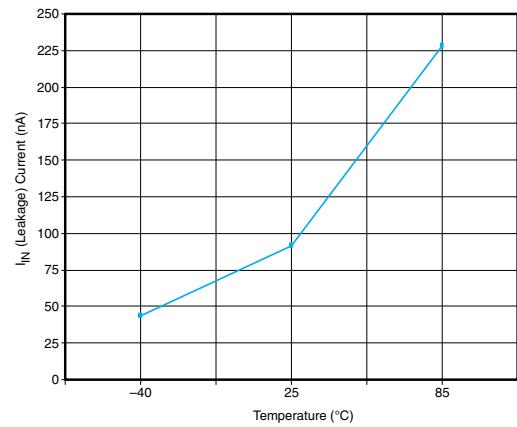
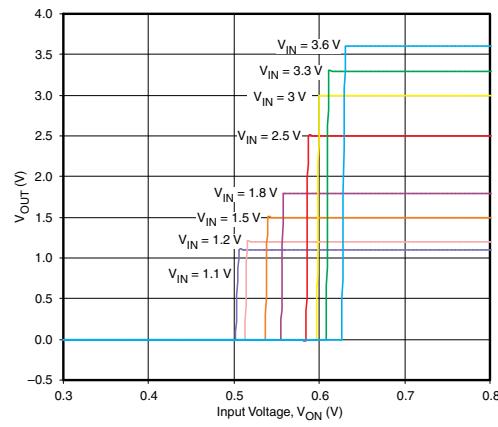


Figure 7-6. $I_{IN(OFF)}$ vs V_{IN} ($V_{ON} = 0$ V)

**Figure 7-7. $I_{IN(OFF)}$ vs Temperature ($V_{IN} = 3.3\text{ V}$)****Figure 7-8. $I_{IN}(Leakage)$ vs V_{IN} ($I_{OUT} = 0$)****Figure 7-9. I_{IN} (Leakage) vs Temperature ($V_{IN} = 3.3\text{ V}$)****Figure 7-10. ON-Input Threshold**

7.12.2 Typical AC Characteristics

7.12.2.1 TPS22901

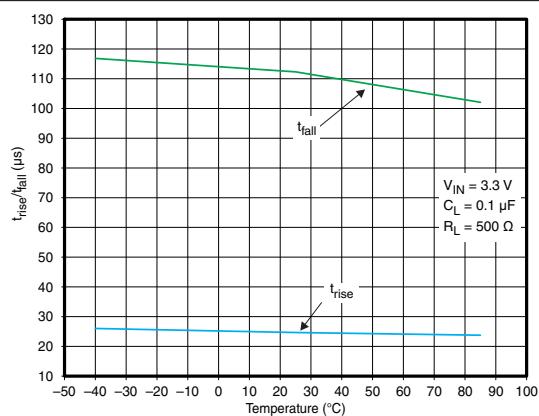


Figure 7-11. t_{rise}/t_{fall} vs Temperature

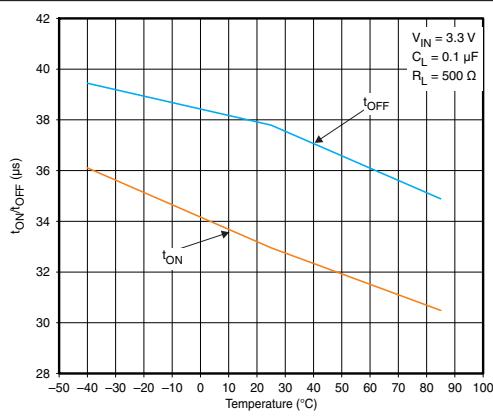


Figure 7-12. t_{ON}/t_{OFF} vs Temperature

7.12.2.2 TPS22902

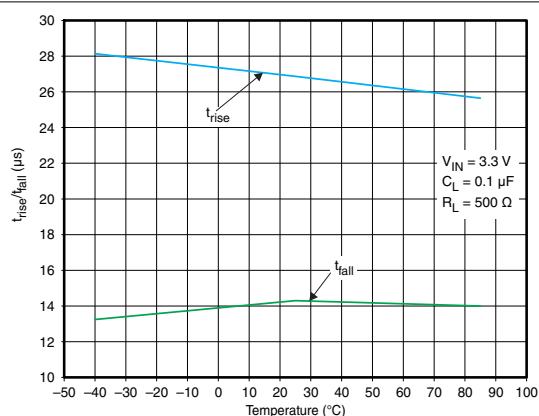


Figure 7-13. t_{rise}/t_{fall} vs Temperature

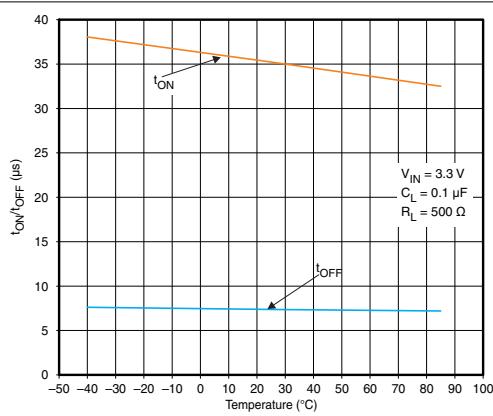


Figure 7-14. t_{ON}/t_{OFF} vs Temperature

7.12.2.3 TPS22902B

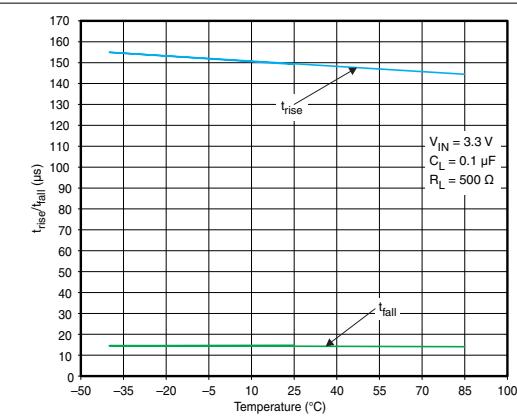


Figure 7-15. t_{rise}/t_{fall} vs Temperature

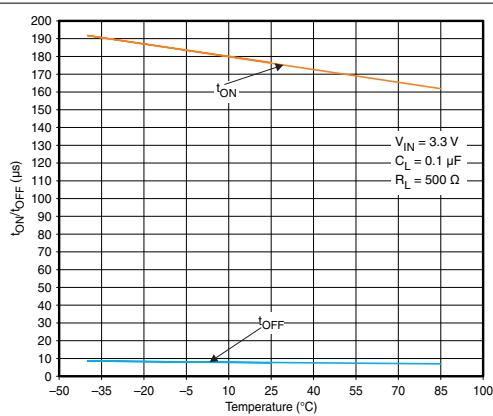
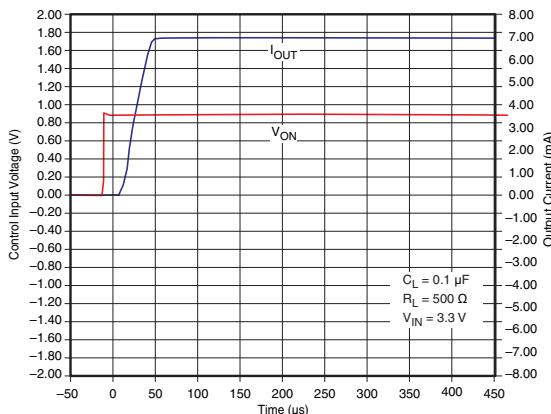
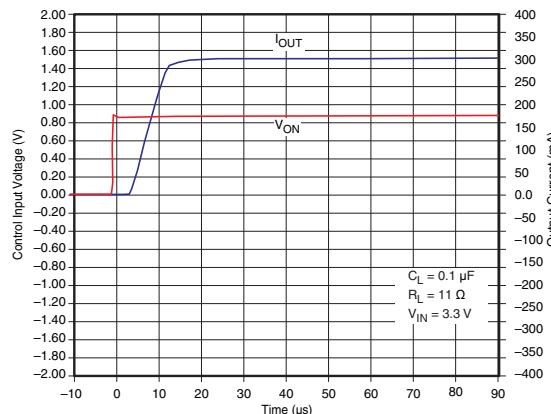
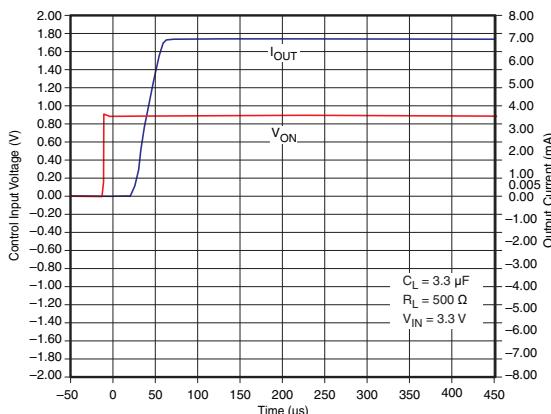
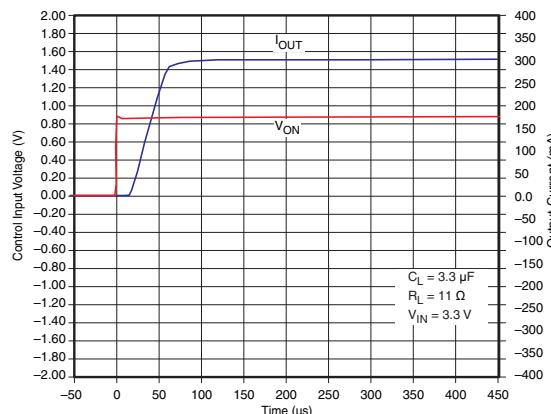
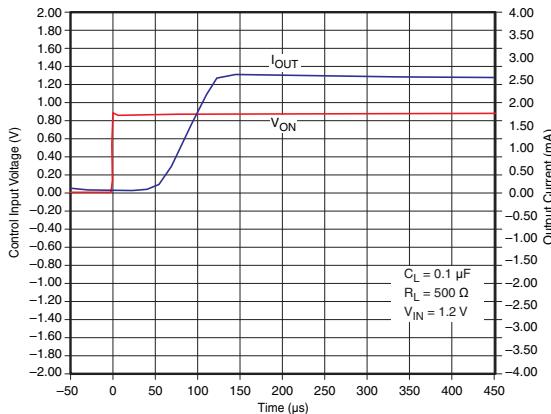
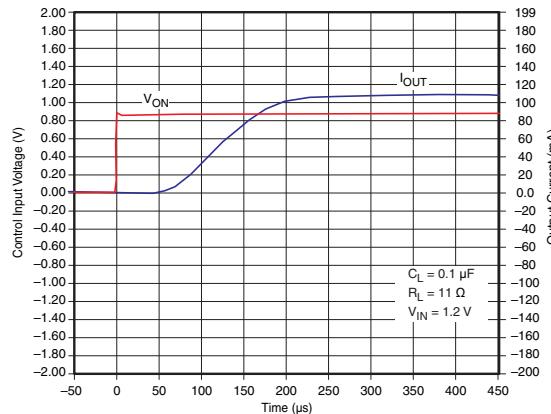


Figure 7-16. t_{ON}/t_{OFF} vs Temperature

7.12.2.4 TPS22901 and TPS22902

Figure 7-17. t_{ON} ResponseFigure 7-18. t_{ON} ResponseFigure 7-19. t_{ON} ResponseFigure 7-20. t_{ON} ResponseFigure 7-21. t_{ON} ResponseFigure 7-22. t_{ON} Response

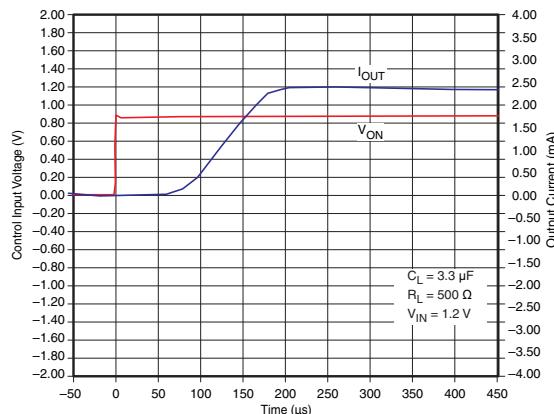


Figure 7-23. t_{ON} Response

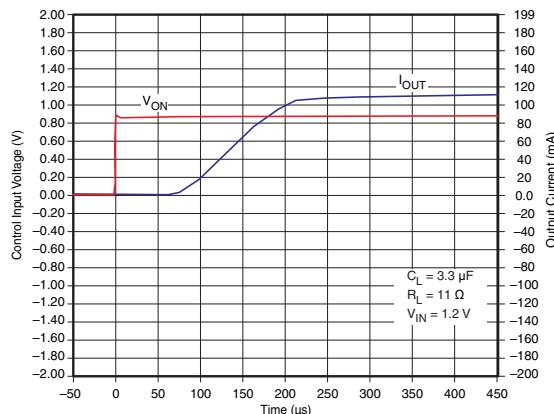


Figure 7-24. t_{ON} Response

7.12.2.5 TPS22901

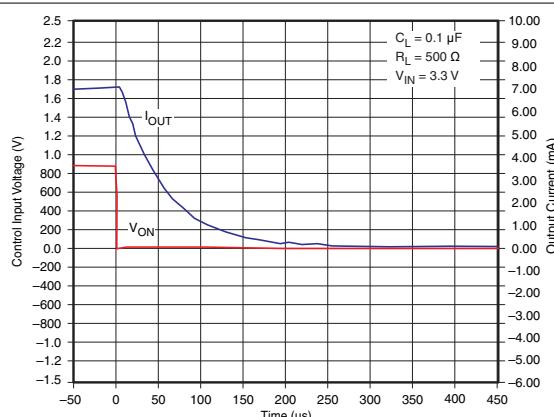


Figure 7-25. t_{OFF} Response

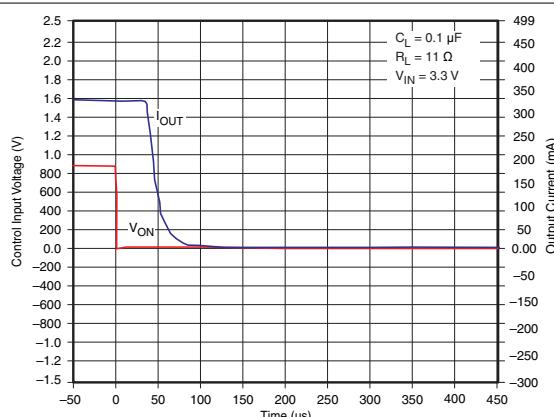


Figure 7-26. t_{OFF} Response

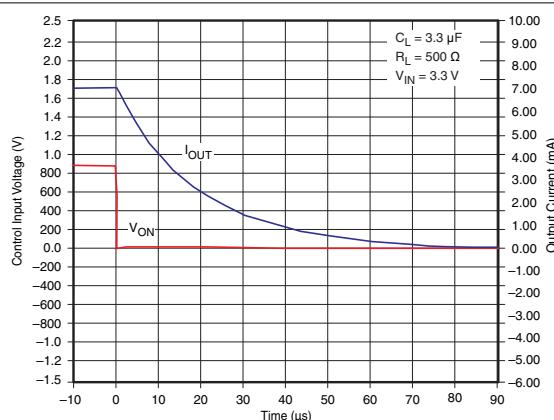


Figure 7-27. t_{OFF} Response

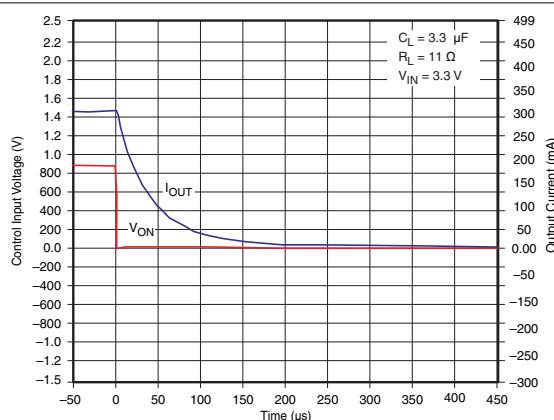
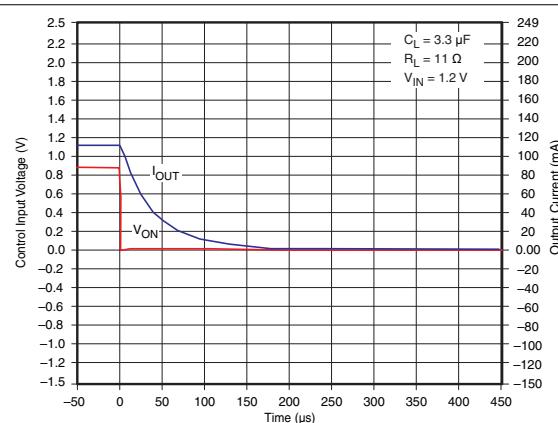
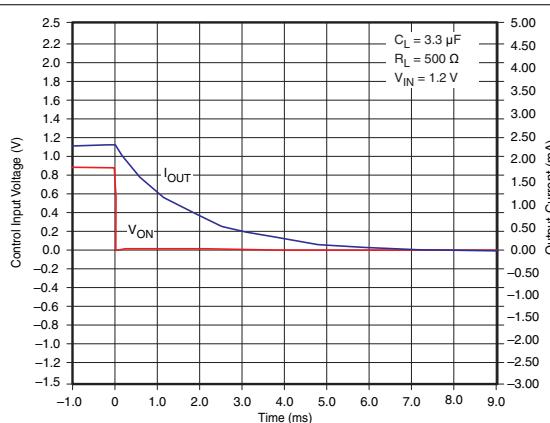
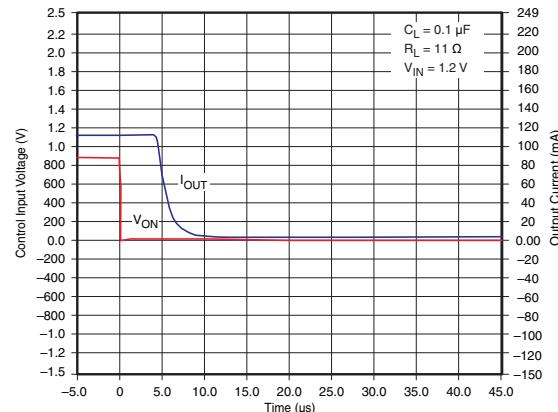
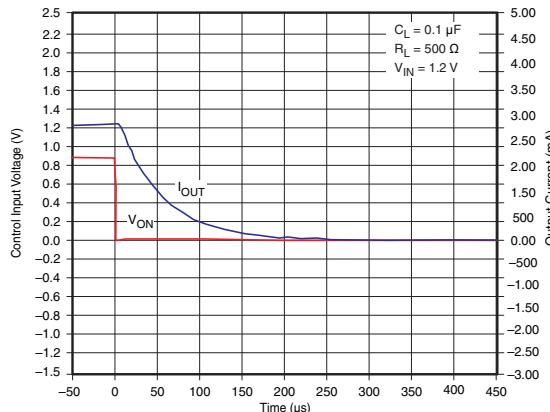
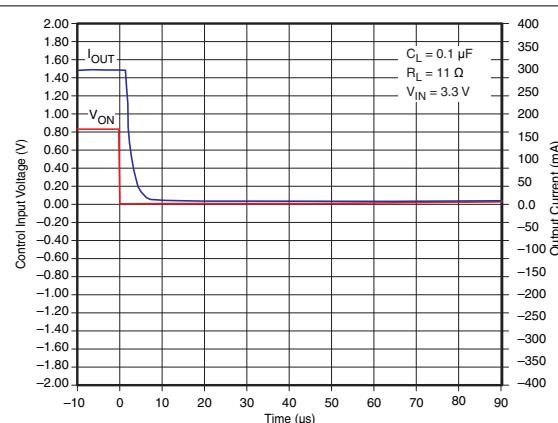
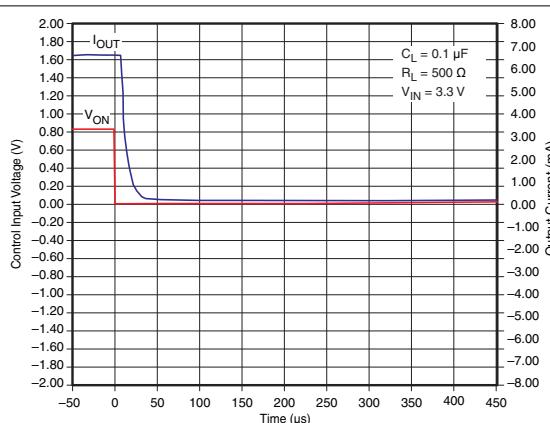


Figure 7-28. t_{OFF} Response



7.12.2.6 TPS22902



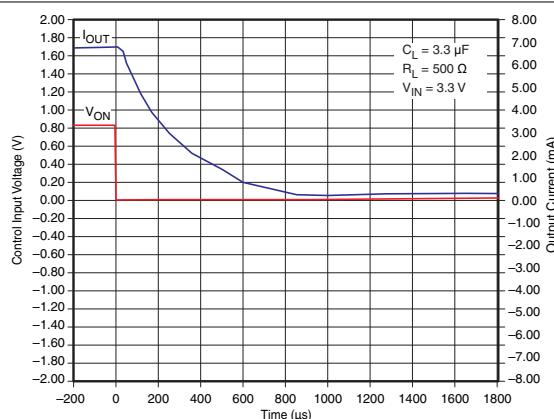


Figure 7-35. t_{OFF} Response

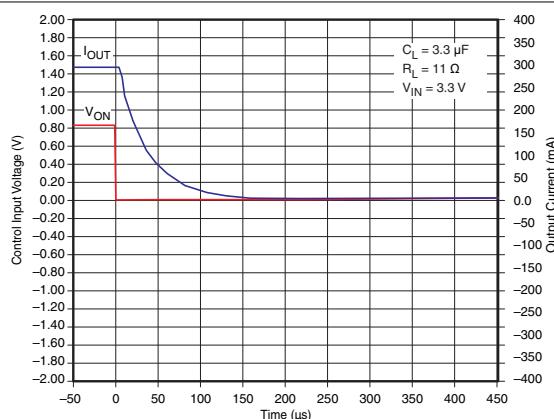


Figure 7-36. t_{OFF} Response

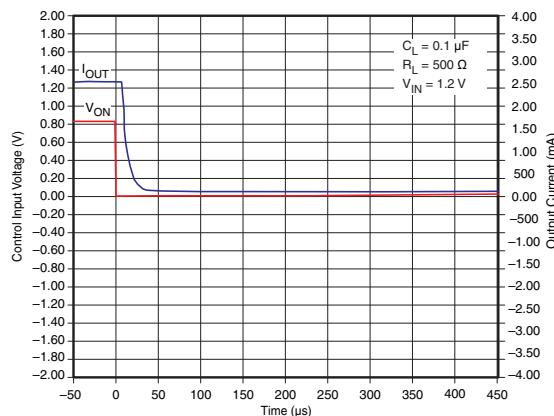


Figure 7-37. t_{OFF} Response

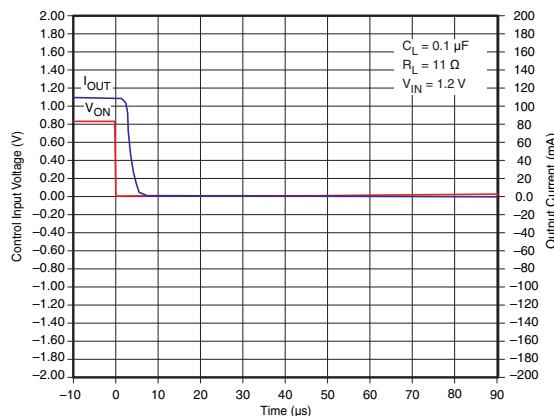


Figure 7-38. t_{OFF} Response

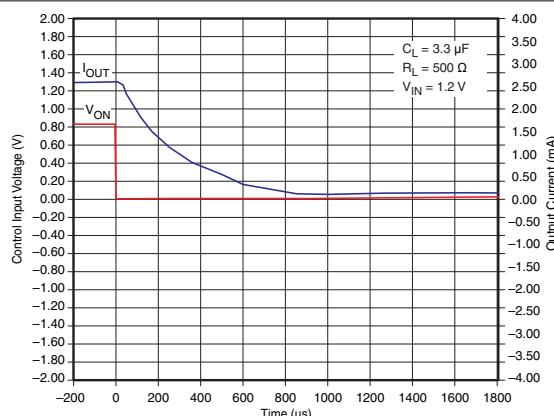


Figure 7-39. t_{OFF} Response

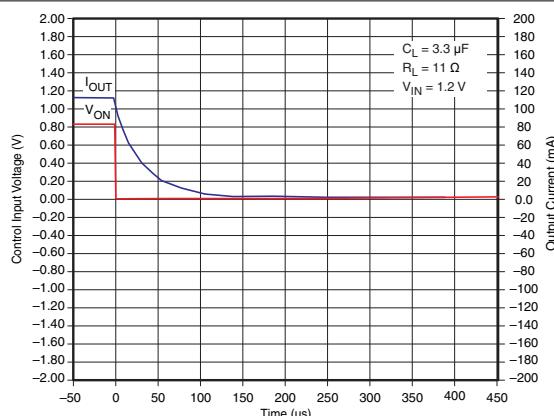
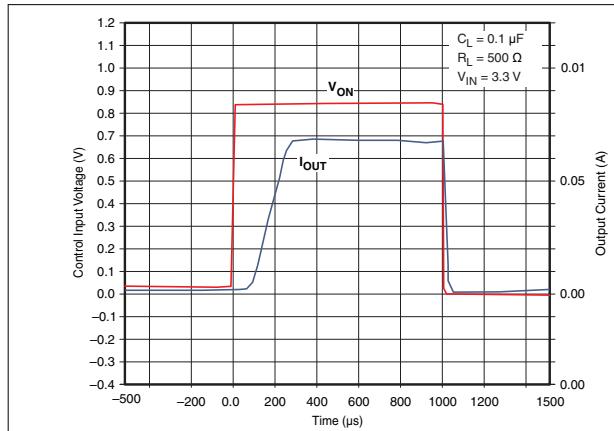
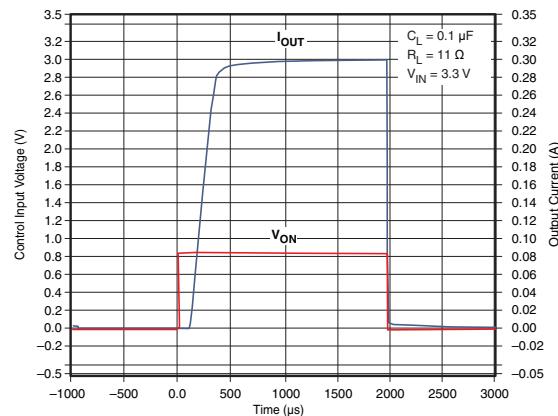
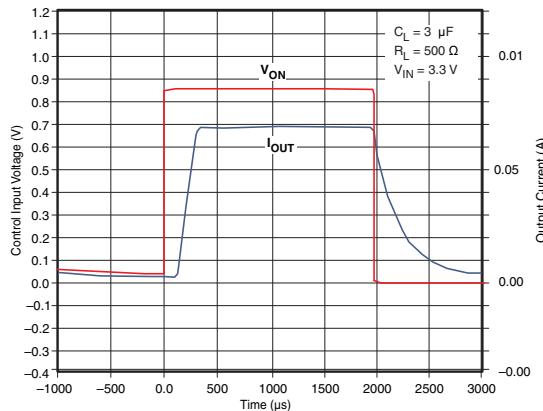
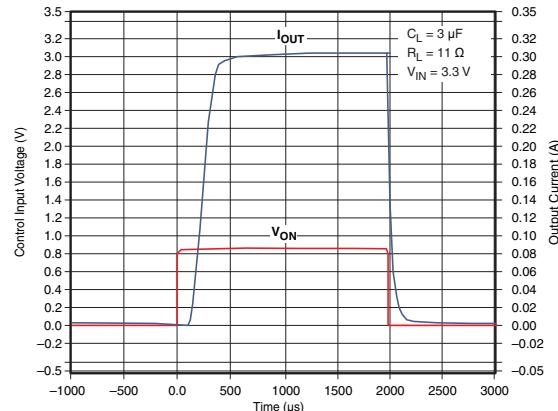
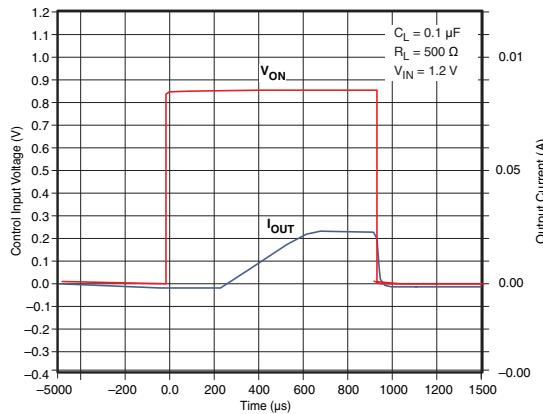
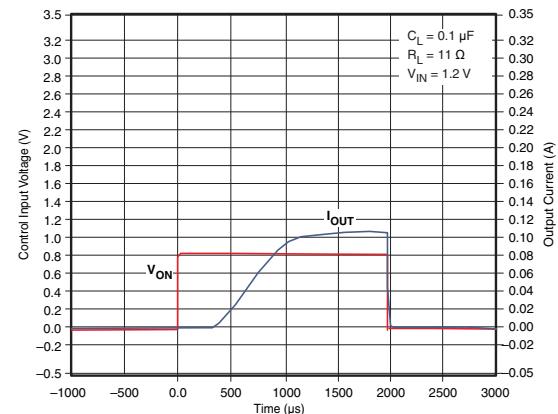


Figure 7-40. t_{OFF} Response

7.12.2.7 TPS22902B

Figure 7-41. t_{ON} ResponseFigure 7-42. t_{ON} ResponseFigure 7-43. t_{ON} ResponseFigure 7-44. t_{ON} ResponseFigure 7-45. t_{ON} ResponseFigure 7-46. t_{ON} Response

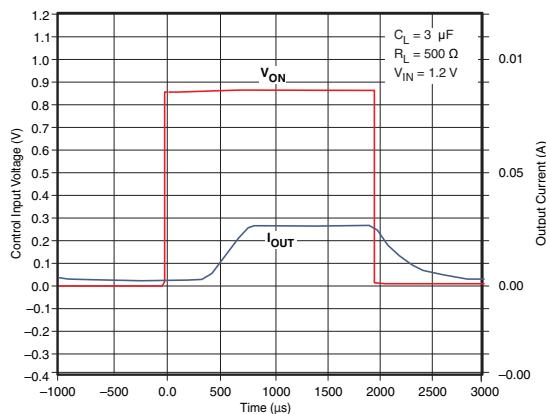


Figure 7-47. t_{ON} Response

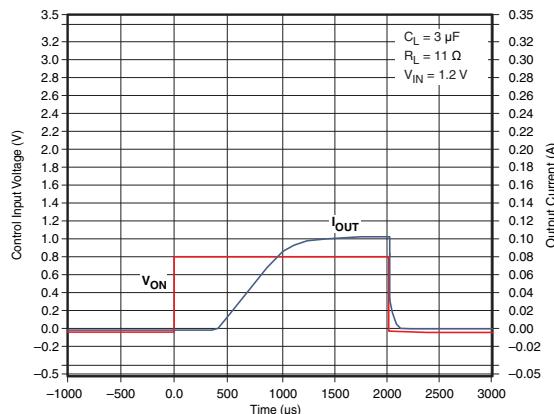


Figure 7-48. t_{ON} Response

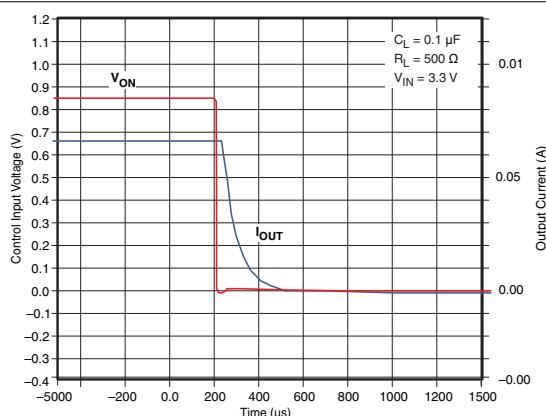


Figure 7-49. t_{OFF} Response

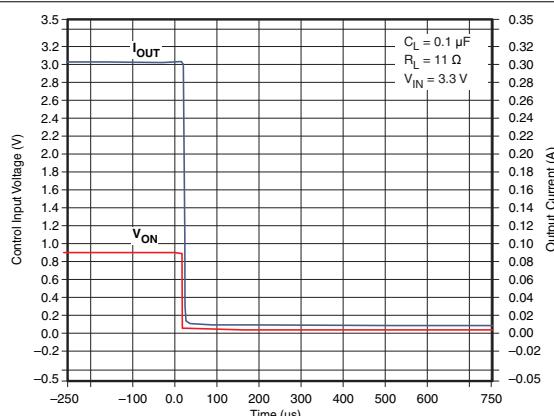


Figure 7-50. t_{OFF} Response

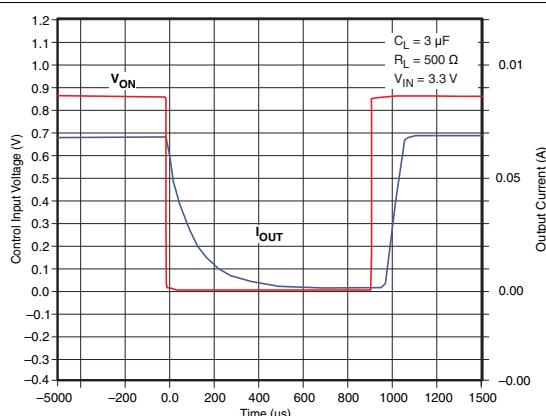


Figure 7-51. t_{OFF} Response

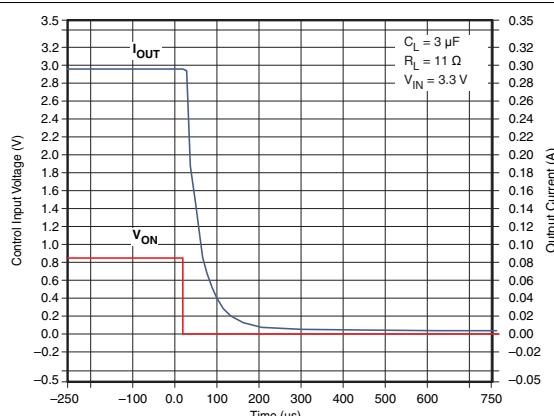
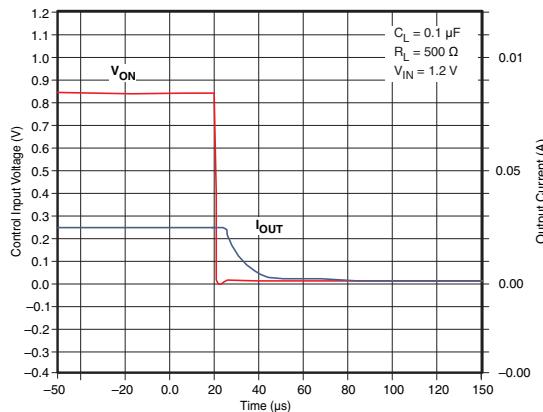
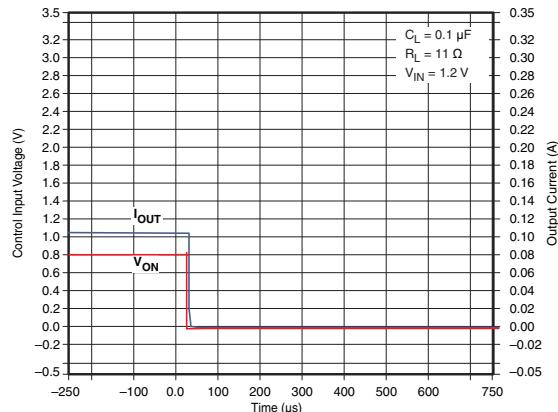
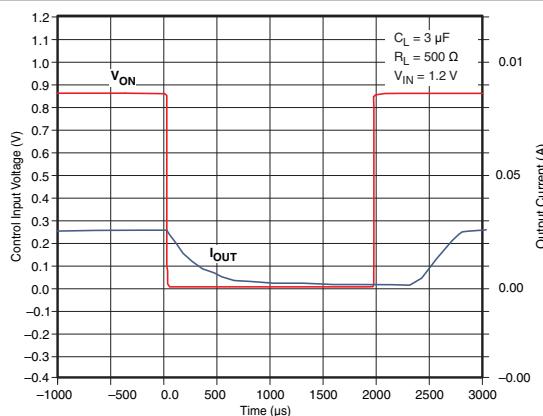
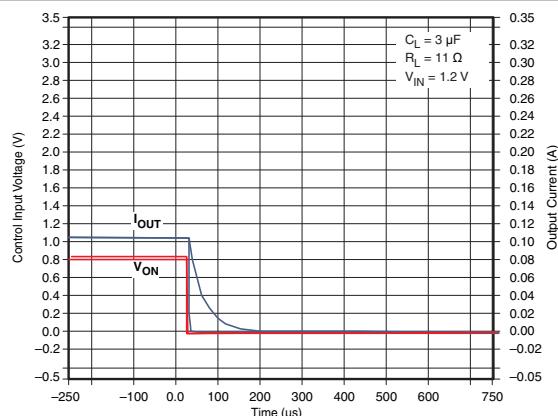
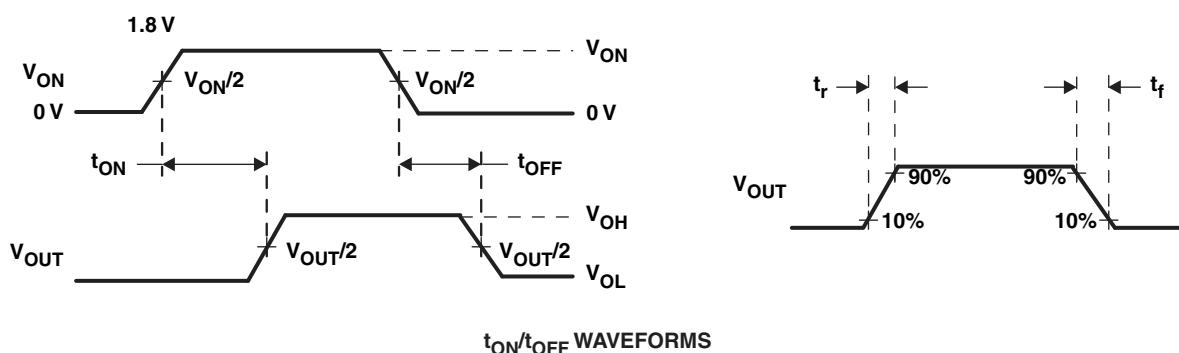
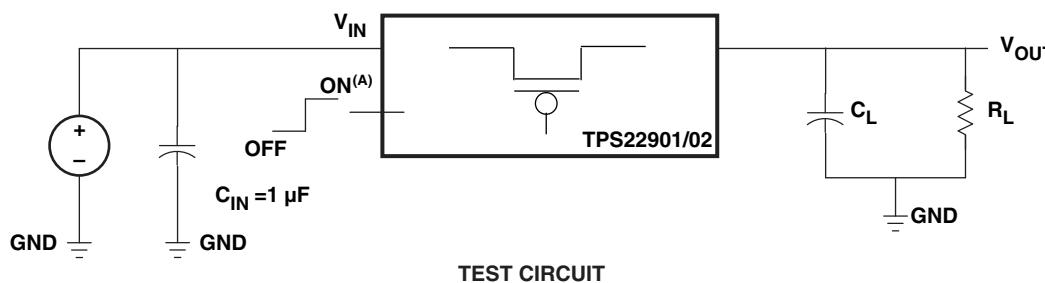


Figure 7-52. t_{OFF} Response

**Figure 7-53. t_{OFF} Response****Figure 7-54. t_{OFF} Response****Figure 7-55. t_{OFF} Response****Figure 7-56. t_{OFF} Response**

8 Parameter Measurement Information



A. t_{rise} and t_{fall} of the control signal is 100 ns.

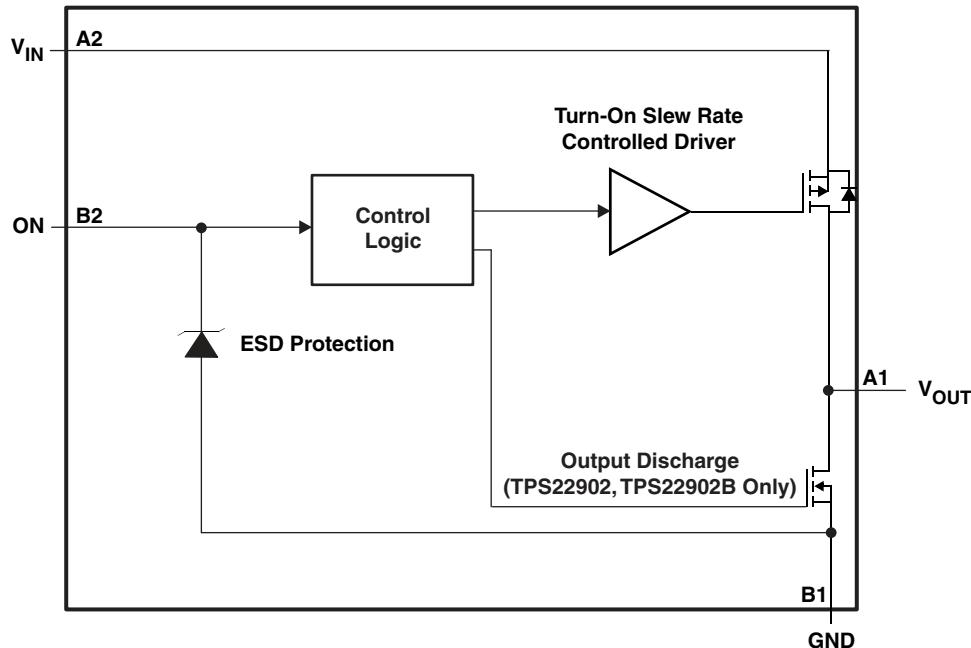
Figure 8-1. Test Circuit and t_{ON}/t_{OFF} Waveforms

9 Detailed Description

9.1 Overview

The TPS2290x and TPS22902B is a single channel, 500-mA load switch in a small, space-saving DSBGA-4 package. These devices implement a P-channel MOSFET to provide a low ON-resistance for a low voltage drop across the device. A controlled rise time is used in applications to limit the inrush current.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 ON/OFF Control

The ON pin controls the state of the switch. Activating ON continuously holds the switch in the on state. ON is active-high and has a low threshold, making it capable of interfacing with low-voltage signals. The ON pin is compatible with standard GPIO logic threshold, and it can be used with any microcontroller with 1.2 V, 1.8 V, 2.5 V or 3.3 V GPIOs.

9.3.2 Quick Output Discharge

The TPS2290x and TPS22902B includes the Quick Output Discharge (QOD) feature. When the switch is disabled, a discharge resistance with a typical value of $88\ \Omega$ is connected between the output and ground. This resistance pulls down the output and prevents it from floating when the device is disabled.

9.4 Device Functional Modes

Table 9-1 lists the VOUT pin connections for a particular device as determined by the ON pin.

Table 9-1. VOUT Function Table

ON (Control Input)	TPS22901	TPS22902/2B
L	Open	GND
H	VIN	VIN

10 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

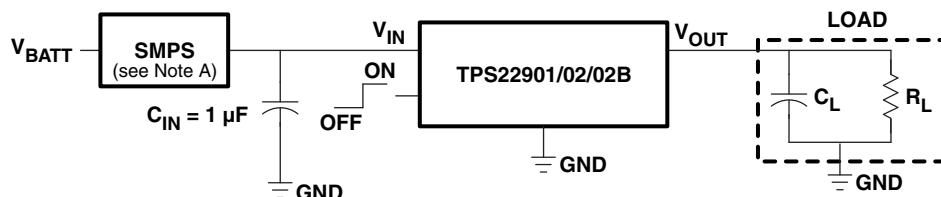
10.1.1 Input Capacitor (Optional)

To limit the voltage drop on the input supply caused by transient inrush currents when the switch turns on into a discharged load capacitor, a capacitor needs to be placed between V_{IN} and GND. A 1- μ F ceramic capacitor, C_{IN} , placed close to the pins is usually sufficient. Higher values of C_{IN} can be used to further reduce the voltage drop during high current application. When switching heavy loads, TI recommends using an input capacitor about 10 times higher than the output capacitor in order to avoid excessive voltage drop.

10.1.2 Output Capacitor (Optional)

Because of the integral body diode in the PMOS switch, a C_{IN} greater than C_L is highly recommended. A C_L greater than C_{IN} can cause V_{OUT} to exceed V_{IN} when the system supply is removed. This could result in current flow through the body diode from V_{OUT} to V_{IN} .

10.2 Typical Application



A. Switched-mode power supply

Figure 10-1. Typical Application Schematic

10.2.1 Design Requirements

Table 10-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
V_{IN}	1.8 V
C_L	4.7 μ F
Load current	500 mA
Ambient Temperature	25 °C
Maximum inrush current	200 mA

10.2.2 Detailed Design Procedure

10.2.2.1 Managing Inrush Current

When the switch is enabled, the output capacitors must be charged up from 0 V to the set value (1.8 V in this example). This charge arrives in the form of inrush current. Inrush current can be calculated using the following equation:

$$I_{\text{INRUSH}} = C_L \times \frac{dV_{\text{OUT}}}{dt} \quad (1)$$

where:

- C_L = Output capacitance
- dV_{OUT} = Output voltage
- dt = Rise time

The TPS2290x and TPS22902B offers a controlled rise time for minimizing inrush current. This device can be selected based upon the minimum acceptable rise time which can be calculated using the design requirements and the inrush current equation. An output capacitance of 4.7 μF will be used since the amount of inrush current increases with output capacitance:

$$\begin{aligned} 200 \text{ mA} &= 4.7 \mu\text{F} \times 1.8\text{V} / dt \\ dt &= 42.3 \mu\text{s} \end{aligned} \quad (2)$$

To ensure an inrush current of less than 200 mA, a device with a rise time greater than 42.3 μs must be used. The TPS22902B has a typical rise time of 220 μs at 1.8 V which meets the above design requirements. The TPS22901/2 has a faster rise time of 40 μs at 1.8 V, and this would result in an inrush current larger than desired.

10.2.2.2 VIN to VOUT Voltage Drop

The voltage drop from VIN to VOUT is determined by the ON-resistance of the device and the load current. R_{ON} can be found in [Section 7.5](#) and is dependent on temperature. When the value of R_{ON} is found, the following equation can be used to calculate the voltage drop across the device:

$$\Delta V = I_{\text{LOAD}} \times R_{\text{ON}} \quad (3)$$

where:

- ΔV = Voltage drop across the device
- I_{LOAD} = Load current
- R_{ON} = ON-resistance of the device

At $V_{\text{IN}} = 1.8$ V, the TPS22901/2/2B has an R_{ON} value of 109 m Ω . Using this value and the defined load current, the above equation can be evaluated:

$$\begin{aligned} \Delta V &= 500 \text{ mA} \times 109 \text{ m}\Omega \\ \Delta V &= 54.5 \text{ mV} \end{aligned} \quad (4)$$

Therefore, the voltage drop across the device will be 54.5 mV.

10.2.3 Application Curve

Figure 10-2 shows the expected voltage drop across the device for different load currents and input voltages.

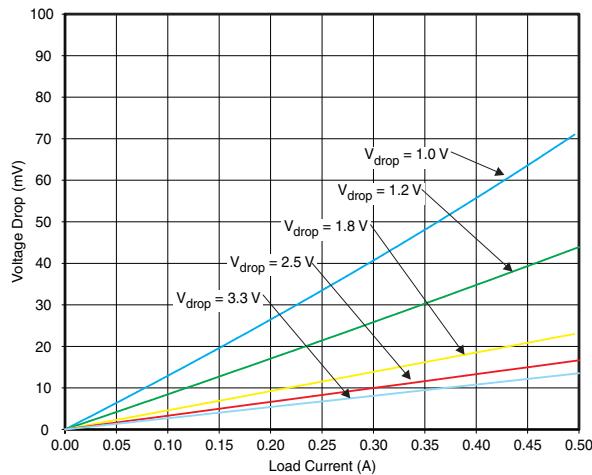


Figure 10-2. Voltage Drop vs Load Current

11 Power Supply Recommendations

The device is designed to operate with a VIN range of 1 V to 3.6 V. This supply must be well regulated and placed as close to the device terminals as possible. It must also be able to withstand all transient and load currents, using a recommended input capacitance of 1 μ F if necessary. If the supply is located more than a few inches from the device terminals, additional bulk capacitance may be required in addition to the ceramic bypass capacitors. If additional bulk capacitance is required, an electrolytic, tantalum, or ceramic capacitor of 10 μ F may be sufficient.

12 Layout

12.1 Layout Guidelines

For best performance, V_{IN} , V_{OUT} , and GND traces should be as short and wide as possible to help minimize the parasitic electrical effects. To be most effective, the input and output capacitors should be placed close to the device to minimize the effects that parasitic trace inductances may have on normal operation.

For higher reliability, the maximum IC junction temperature, $T_{J(max)}$, should be restricted to 125°C under normal operating conditions. Junction temperature is directly proportional to power dissipation in the device and the two are related by

$$T_J = T_A + \theta_{JA} \times P_D \quad (5)$$

where:

- T_J = Junction temperature of the device
- T_A = Ambient temperature
- P_D = Power dissipation inside the device
- θ_{JA} = Junction to ambient thermal resistance. See Thermal Information section of the datasheet. This parameter is highly dependent on board layout.

12.2 Layout Example

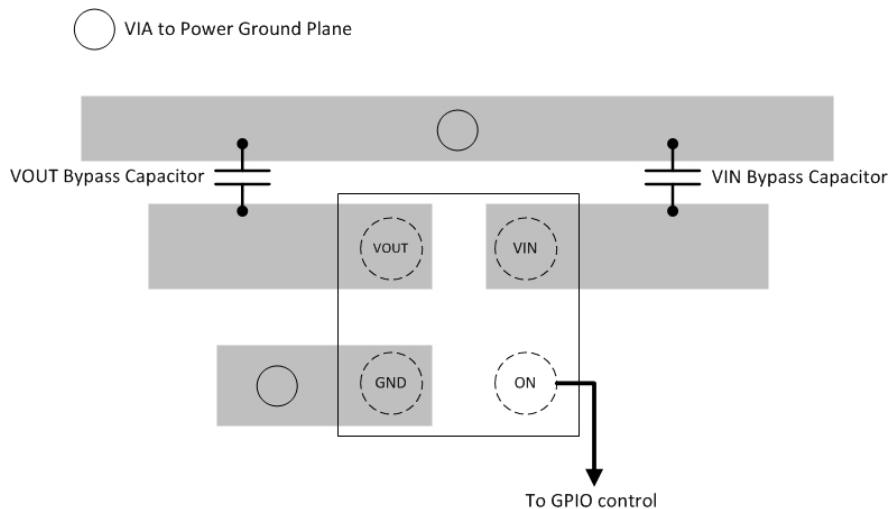


Figure 12-1. Layout Example Schematic

13 Device and Documentation Support

13.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 13-1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TPS22901	Click here				
TPS22902	Click here				
TPS22902B	Click here				

13.2 Trademarks

All other trademarks are the property of their respective owners.

13.3 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

13.4 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS22901YFPR	ACTIVE	DSBGA	YFP	4	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	3P (3, 5)	Samples
TPS22902BYFPR	ACTIVE	DSBGA	YFP	4	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	3S 3	Samples
TPS22902YFPR	ACTIVE	DSBGA	YFP	4	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	3R	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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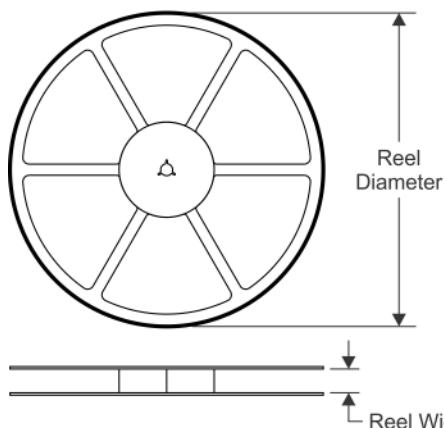
PACKAGE OPTION ADDENDUM

10-Dec-2020

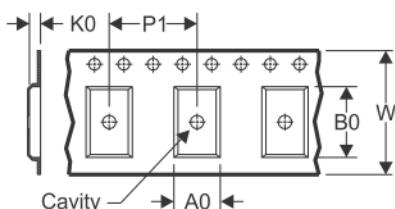
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

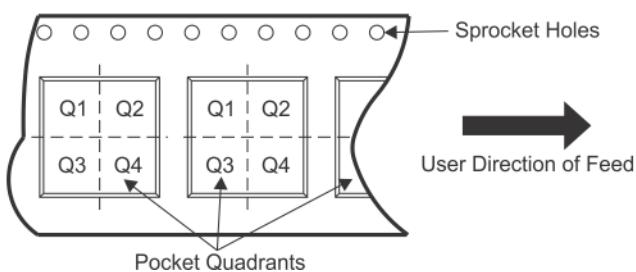


TAPE DIMENSIONS



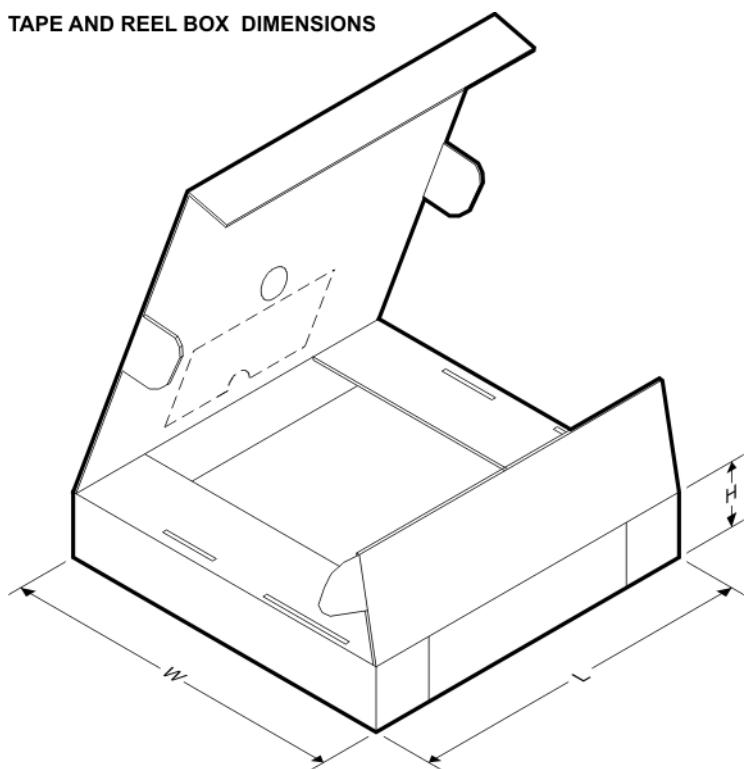
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS22901YFPR	DSBGA	YFP	4	3000	178.0	9.2	0.89	0.89	0.58	4.0	8.0	Q1
TPS22902BYFPR	DSBGA	YFP	4	3000	180.0	8.4	0.89	0.89	0.58	4.0	8.0	Q1
TPS22902YFPR	DSBGA	YFP	4	3000	178.0	9.2	0.89	0.89	0.58	4.0	8.0	Q1
TPS22902YFPR	DSBGA	YFP	4	3000	180.0	8.4	0.89	0.89	0.58	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS22901YFPR	DSBGA	YFP	4	3000	220.0	220.0	35.0
TPS22902BYFPR	DSBGA	YFP	4	3000	182.0	182.0	20.0
TPS22902YFPR	DSBGA	YFP	4	3000	270.0	225.0	227.0
TPS22902YFPR	DSBGA	YFP	4	3000	182.0	182.0	20.0

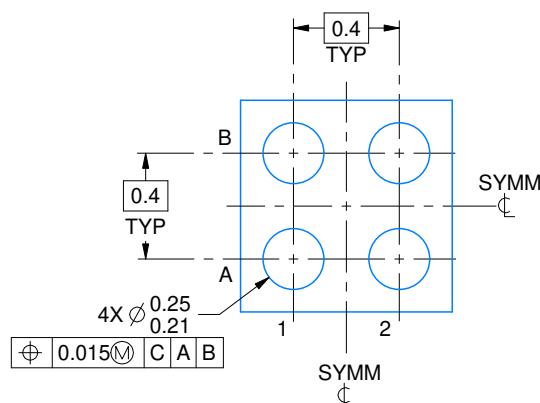
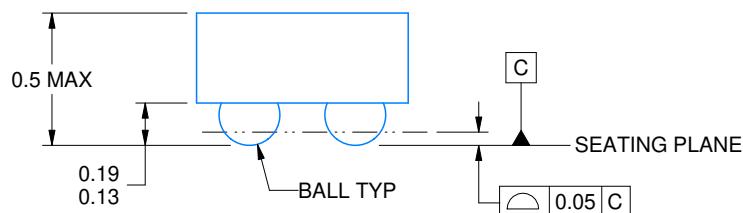
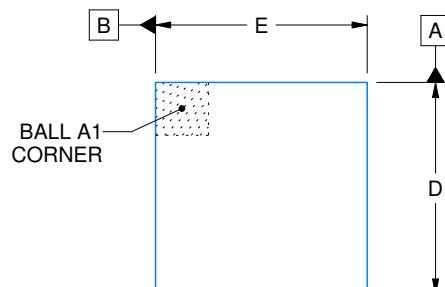
PACKAGE OUTLINE

YFP0004



DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



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NOTES:

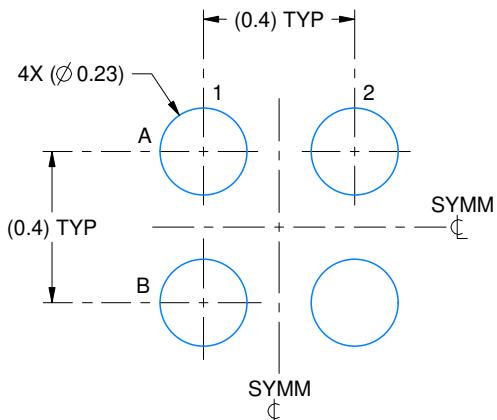
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

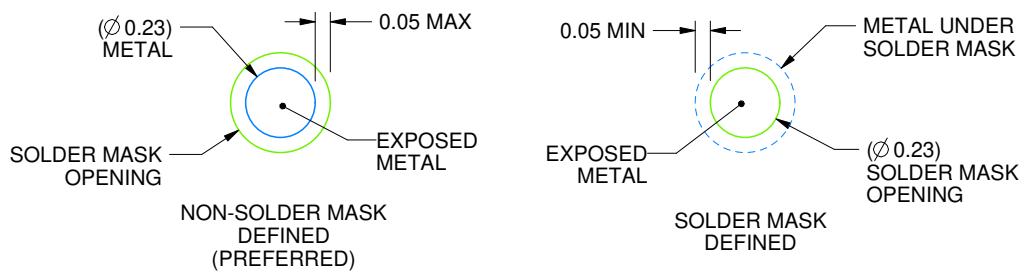
YFP0004

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:50X



SOLDER MASK DETAILS
NOT TO SCALE

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NOTES: (continued)

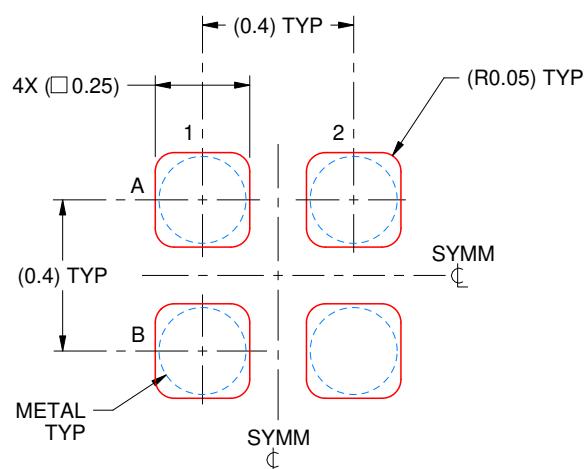
- Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints.
For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

EXAMPLE STENCIL DESIGN

YFP0004

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



**SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:50X**

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NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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